TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# T C 7 W 2 4 1 F U

# **NON-INVERTED, 3-STATE OUTPUTS**

The TC7W241FU is a high speed C<sup>2</sup>MOS DUAL BUS BUFFERS fabricated with silicon gate C<sup>2</sup>MOS technology. It achieve the high speed operation similar to equivalent LSTTL while maintaining the C<sup>2</sup>MOS low power dissipation.

It is a non-inverting 3-state buffer has one active-high and one active-low output enable.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.



• High Speed  $\cdots$   $t_{pd} = 10$ ns (Typ.) at  $V_{CC} = 5V$ 

• Low Power Dissipation  $\cdots I_{CC} = 2\mu A$  (Max.) at Ta = 25°C

• High Noise Immunity ...... V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (Min.)

• Output Drive Capability ...... 15 LSTTL Loads

• Symmetrical Output Impedance… |IOH| = IOL = 6mA (Min.)

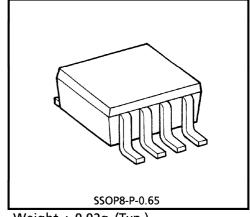
Balanced Propagation Delays ······ t<sub>pLH</sub>≒t<sub>pHL</sub>

Wide Operating Voltage Range··· V<sub>CC</sub> (opr) = 2~6V

#### **MAXIMUM RATINGS**

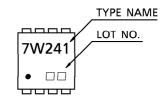
PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	Vcc	-0.5~7	V
DC Input Voltage	VIN	-0.5~V <sub>CC</sub> +0.5	V
DC Output Voltage	Vout	-0.5~V <sub>CC</sub> +0.5	V
Input Diode Current	ΙΚ	± 20	mA
Output Diode Current	loк	± 20	mA
DC Output Current	IOUT	± 35	mΑ
DC V <sub>CC</sub> /Ground Current	Icc	± 37.5	mA
Power Dissipation	PD	300	mW
Storage Temperature	T <sub>stg</sub>	<b>-65∼150</b>	°C
Lead Temperature (10s)	TL	260	°C

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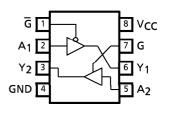


Weight: 0.02g (Typ.)

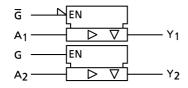
#### **MARKING**



PIN ASSIGNMENT (TOP VIEW)



## **LOGIC DIAGRAM**



## TRUTH TABLE

	INPUT	OUTPUT	
G	G	Α	Υ
L	Н	L	L
L	Н	Н	Н
Н	L	Х	Z

X : Don't Care Z : High Impedance

## **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	Vcc	2~6	V
Input Voltage	V <sub>IN</sub>	0~V <sub>CC</sub>	٧
Output Voltage	Vout	0~V <sub>CC</sub>	>
Operating Temperature	T <sub>opr</sub>	<b>-40∼85</b>	Ç
		$0\sim1000 \text{ (V}_{CC}=2.0\text{V)}$	
Input Rise and Fall Time	t <sub>r</sub> , t <sub>f</sub>	$0 \sim 500 \text{ (V}_{CC} = 4.5\text{V)}$ $0 \sim 400 \text{ (V}_{CC} = 6.0\text{V)}$	ns
		0~ 400 (VCC = 6.0V)	

#### DC ELECTRICAL CHARACTERISTICS

DC ELECTRICAL CHARACTERISTICS												
PARAMETER	SYMBOL	TEST	TEST CONDITION			Т	$a = 25^{\circ}$	C	Ta = -4	10∼85°C	LINIT	
PARAIVIETER STIVIBUL		CIR- CUIT	1E31 CONDITION		Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT	
High-Level Input		_	_		2.0	1.5	_	_	1.5	_		
Voltage	$V_{IH}$				4.5	3.15	<b>—</b>	—	3.15	—	V	
Voltage					6.0	4.2	_	_	4.2			
Low-Level Input			_		2.0	—	<b>—</b>	0.5	—	0.5		
Voltage	V <sub>IL</sub>	—			4.5	—	_	1.35	—	1.35	V	
L					6.0			1.8		1.8		
			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -20μA	2.0	1.9	2.0	<b> </b>	1.9	_	v	
High-Level		_			4.5	4.4	4.5	<b> </b>	4.4	_		
Output Voltage	VOH				6.0	5.9	6.0	_	5.9	_		
Catput voltage				$I_{OH} = -6mA$	4.5	4.18	4.31	<b>—</b>	4.13	<u> </u>		
				$I_{OH} = -7.8 \text{mA}$	6.0	5.68	5.80	_	5.63			
			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 20μΑ	2.0	—	0.0	0.1	—	0.1		
Low-Level					4.5	—	0.0	0.1	—	0.1		
Output Voltage	VOL	_			6.0		0.0	0.1	_	0.1	V	
Toutput voltage				IOL = 6mA	4.5	—	0.17	0.26	—	0.33		
				$I_{OL} = 7.8 \text{mA}$	6.0	_	0.18	0.26	_	0.33		
3-State Output Off-State Current	loz	_	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>OUT</sub> = V <sub>CC</sub> or GND		6.0	_	_	± 0.5	_	± 5.0		
Input Leakage Current	I <sub>IN</sub>		V <sub>IN</sub> = V <sub>CC</sub> or GND		6.0			±0.1	_	± 1.0	$\mu$ A	
Quiescent Supply Current	lcc	_	V <sub>IN</sub> = V <sub>CC</sub> or GND		6.0	_	_	2.0	_	20.0		

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## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 6ns$ )

PARAMETER	SYMBOL	TEST	TEST			Ta = 25°C			Ta = − 40~85°C		
FARAIVIETER STIVIBUL		CIR- CUIT	CONDITION	CL	V <sub>C</sub> C	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
Output Transition	t				2.0	_	25	60	_	75	
Time	t <sub>TLH</sub>	_	_	50	4.5	_	7	12	—	15	
Tillie	<sup>t</sup> THL				6.0	_	6	10	_	13	
					2.0	_	36	90	_	115	
				50	4.5	_	12	18	—	23	
Propagation	<sup>t</sup> PLH		_		6.0	_	10	15	_	20	
Delay Time	<sup>t</sup> pHL		_		2.0	_	51	130	_	165	
				150	4.5	_	17	26	_	33	
					6.0		14	22	_	28	ns
	<sup>t</sup> pZL	_	$R_L = 1k\Omega$		2.0	_	48	125	_	155	115
Output Enable Time				50	4.5		16	25	—	31	-
					6.0	_	14	21	_	26	
	t <sub>p</sub> ZH			150	2.0	_	63	165	_	205	
					4.5	_	21	33	—	41	
					6.0		18	28	_	35	
Output Disable	<sup>t</sup> pLZ				2.0	_	32	125	—	155	
Time		—	$R_L = 1k\Omega$	50	4.5		15	25	l —	31	
	<sup>t</sup> pHZ				6.0		14	21	_	26	
Input Capacitance	CIN	_	_	_	_	_	5	10	_	10	
Output Capacitance	COUT	_	_				10				рF
Power Dissipation Capacitance	C <sub>PD</sub>	_	Note (1)	_	_	_	33	_	_	_	

Note (1): CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

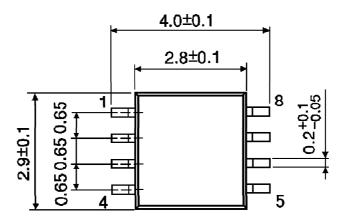
Average operating current can be obtained by the equation:

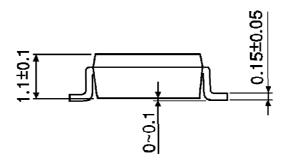
ICC (opr) = CPD·VCC·fIN + ICC / 2 (per Gate)

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# PACKAGE DIMENSIONS

SSOP8-P-0.65 Unit: mm





Weight: 0.02g (Typ.)

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